

# KA1M0565R/KA1H0565R

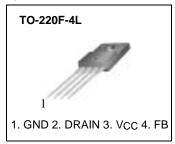
# Fairchild Power Switch(FPS)

#### **Features**

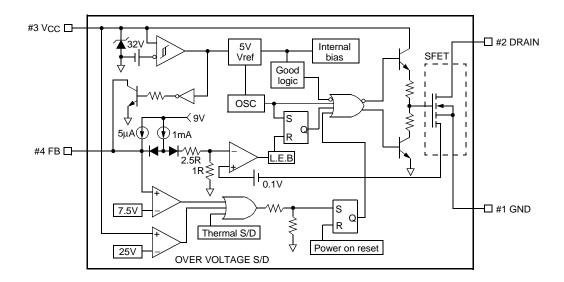
- · Precision fixed operating frequency
- KA1M0565R (67KHz),KA1H0565R (100KHz)
- · Pulse by pulse over current limiting
- · Over load protection
- Over voltage protection (Min. 23V)
- Internal thermal shutdown function
- Under voltage lockout
- · Internal high voltage sense FET
- · Auto restart

### **Description**

The Fairchild Power Switch(FPS) product family is specially designed for an off-line SMPS with minimal external components. The Fairchild Power Switch(FPS) consist of high voltage power SenseFET and current mode PWM controller IC. PWM controller features integrated fixed oscillator, under voltage lock out, leading edge blanking, optimized gate turn-on/turn-off driver, thermal shut down protection, over voltage protection, temperature compensated precision current sources for loop compensation and fault protection circuit. compared to discrete MOSFET and controller or RCC switching converter solution, a Fairchild Power Switch(FPS) can reduce total component count, design size, weight and at the same time increase & efficiency, productivity, and system reliability. It has a basic platform well suited for cost effective design in either a flyback converter or a forward converter.



## **Internal Block Diagram**



## **Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Maximum Drain voltage (1)	V <sub>D,MAX</sub>	650	V
Drain Gate voltage (R <sub>GS</sub> =1MΩ)	VDGR	650	V
Gate-source (GND) voltage	VGS	±30	V
Drain current pulsed (2)	I <sub>DM</sub>	20	ADC
Single pulsed avalanche energy (3)	EAS	230	mJ
Continuous drain current (T <sub>C</sub> =25°C)	ID	5.0	ADC
Continuous drain current (Tc=100°C)	ID	3.5	ADC
Maximum Supply voltage	VCC,MAX	30	V
Input voltage range	VFB	-0.3 to VSD	V
Total navyar dissination	PD	140	W
Total power dissipation	Derating	1.11	W/°C
Operating ambient temperature	TA	−25 to +85	°C
Storage temperature	TSTG	-55 to +150	°C

#### Notes:

- 1. Tj=25°C to 150°C
- 2. Repetitive rating: Pulse width limited by maximum junction temperature
- 3. L=30mH, V<sub>DD</sub>=50V, R<sub>G</sub>= 27 $\Omega$ , starting Tj=25°C

## **Electrical Characteristics (SFET part)**

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Drain source breakdown voltage	BVDSS	VGS=0V, ID=50μA	650	-	-	V
Zero gate voltage drain current	IDSS	VDS=Max., Rating, VGS=0V	-	-	50	μΑ
		V <sub>DS</sub> =0.8Max., Rating, V <sub>GS</sub> =0V, T <sub>C</sub> =125°C	-	-	200	μΑ
Static drain source on resistance (note)	RDS(ON)	VGS=10V, ID=2.5A	-	1.76	2.2	Ω
Forward transconductance (note)	gfs	V <sub>DS</sub> =50V, I <sub>D</sub> =2.5A	2.5	-	-	S
Input capacitance	Ciss	VGS=0V, VDS=25V, f=1MHz	-	1457	-	
Output capacitance	Coss		-	130	-	pF
Reverse transfer capacitance	Crss		-	38.8	-	
Turn on delay time	td(on)	V <sub>DD</sub> =0.5BV <sub>DSS</sub> , I <sub>D</sub> =5.0A (MOSFET switching time are essentially independent of operating temperature)	-	-	60	
Rise time	tr		-	-	150	nS
Turn off delay time	td(off)		-	-	300	110
Fall time	tf		-	-	130	
Total gate charge (gate-source+gate-drain)	Qg	VGS=10V, ID=5.0A, VDS=0.5BVDSS (MOSFET switching time are essentially independent of operating temperature)	-	-	56	
Gate source charge	Qgs		-	10.3	-	nC
Gate drain (Miller) charge	Qgd		-	22.3	-	

#### Note:

Pulse test: Pulse width  $\leq 300 \mu S$ , duty cycle  $\leq 2\%$   $S = \frac{1}{R}$ 

## **Electrical Characteristics (CONTROL part)**

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit	
UVLO SECTION							
Start threshold voltage	VSTART	-	14	15	16	V	
Stop threshold voltage	VSTOP	After turn on	9	10	11	V	
OSCILLATOR SECTION							
Initial accuracy	Fosc	KA1M0565R	61	67	73	kHz	
		KA1H0565R	90	100	110		
Frequency change with temperature (2)	ΔΕ/ΔΤ	–25°C ≤ Ta ≤ +85°C	-	±5	±10	%	
Maximum duty cycle	D	KA1M0565R	74	77	80	%	
	Dmax	KA1H0565R	64	67	70		
FEEDBACK SECTION					•		
Feedback source current	lfB	Ta=25°C, 0V ≤ Vfb ≤ 3V	0.7	0.9	1.1	mA	
Shutdown Feedback voltage	VsD	-	6.9	7.5	8.1	V	
Shutdown delay current	Idelay	Ta=25°C, 5V ≤ Vfb ≤ VsD	4.0	5.0	6.0	μΑ	
REFERENCE SECTION							
Output voltage (1)	Vref	Ta=25°C	4.80	5.00	5.20	V	
Temperature Stability (1)(2)	Vref/∆T	–25°C ≤ Ta ≤ +85°C	-	0.3	0.6	mV/°C	
CURRENT LIMIT (SELF-PROTECTION) SECTION							
Peak Current Limit	IOVER	Max. inductor current	3.08	3.5	3.92	Α	
PROTECTION SECTION	PROTECTION SECTION						
Thermal shutdown temperature (Tj) (1)	T <sub>SD</sub>	-	140	160	-	°C	
Over voltage protection voltage	Vovp	-	23	25	28	V	
TOTAL DEVICE SECTION							
Start Up current	ISTART	V <sub>CC</sub> =14V	0.1	0.3	0.4	mA	
Operating supply current (control part only)	IOP	Ta=25°C	6	12	18	mA	
VCC zener voltage	Vz	ICC=20mA	30	32.5	35	V	

#### Note:

- 1. These parameters, although guaranteed, are not 100% tested in production
- 2. These parameters, although guaranteed, are tested in EDS (wafer test) process

## **Typical Performance Characteristics**

(These characteristic graphs are normalized at Ta=25°C)

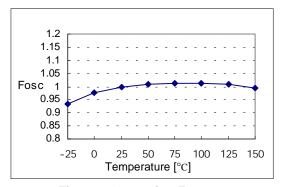


Figure 1. Operating Frequency

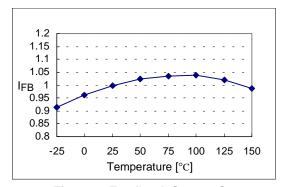
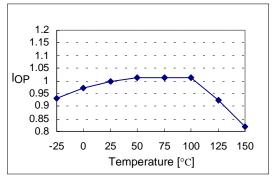


Figure 2. Feedback Source Current



**Figure 3. Operating Supply Current** 

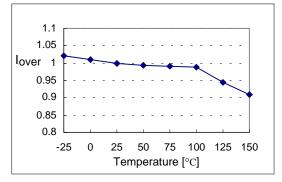


Figure 4. Peak Current Limit

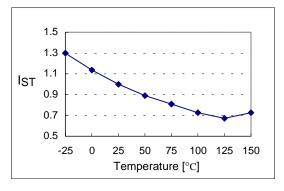


Figure 5. Start up Current

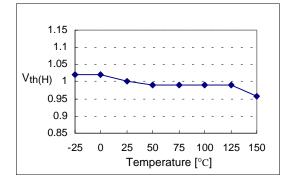


Figure 6. Start Threshold Voltage

### **Typical Performance Characteristics (Continued)**

(These characteristic graphs are normalized at Ta=25°C)

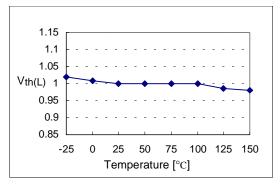


Figure 7. Stop Threshold Voltage

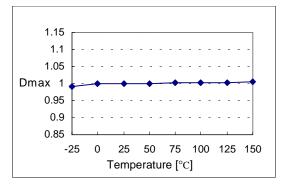


Figure 8. Maximum Duty Cycle

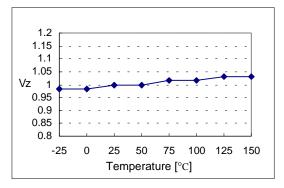


Figure 9. VCC Zener Voltage

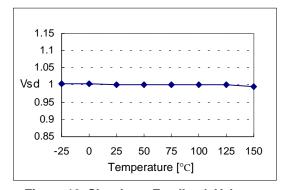


Figure 10. Shutdown Feedback Voltage

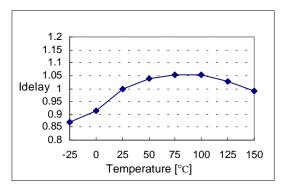


Figure 11. Shutdown Delay Current

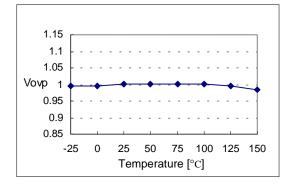


Figure 12. Over Voltage Protection

## **Typical Performance Characteristics** (Continued)

(These characteristic grahps are normalized at Ta=25°C)

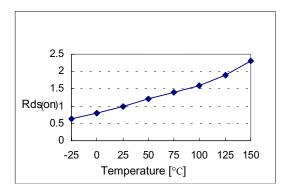
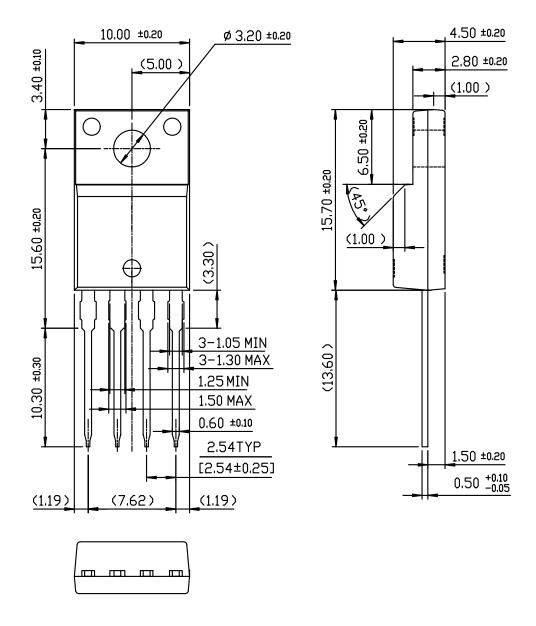


Figure 13. Static Drain-Source on Resistance

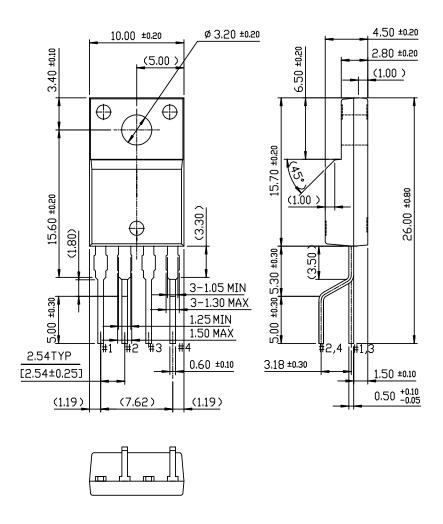
## **Package Dimensions**

## TO-220F-4L



### Package Dimensions (Continued)

# TO-220F-4L(Forming)



### **Ordering Information**

Product Number	Package	Rating	Fosc		
KA1M0565R-TU	TO-220F-4L	650V, 5A	67kHz		
KA1M0565R-YDTU	TO-220F-4L(Forming)	030V, 3A			
KA1H0565R-TU	TO-220F-4L	650V, 5A	100kHz		
KA1H0565R-YDTU	TO-220F-4L(Forming)	030 V, 3A	TOOKITZ		

TU: Non Forming Type YDTU: Forming Type

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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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